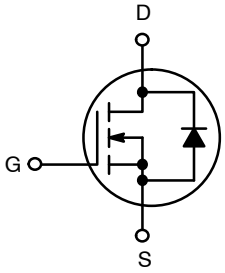
MOSFET – Power, N-Channel, SUPERFET® III, Automotive, Easy-Drive

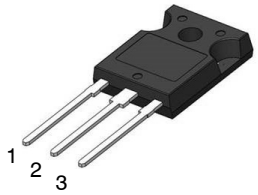
650 V, 65 A, 40 mΩ

NVHL040N65S3

V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
650 V	40 mΩ @ 10 V	65 A



POWER MOSFET



TO-247-3LD
CASE 340CX

Description

SUPERFET III MOSFET is **onsemi**'s brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provides superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III MOSFET Easy drive series helps manage EMI issues and allows for easier design implementation.

Features

- AEC-Q101 Qualified
- 700 V @ T_J = 150 °C
- Typ. $R_{DS(on)}$ = 35.4 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 136 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 1154 pF)
- 100% Avalanche Tested
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Automotive On Board Charger
- Automotive DC/DC Converter for HEV

MARKING DIAGRAM

A	= Assembly Site
YWW	= Date Code (Year & Week)
ZZ	= Assembly Lot Number
NVHL040N65S3	= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25 °C, Unless otherwise noted)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		650	V
V_{GSS}	Gate to Source Voltage	– DC	±30	V
		– AC (f > 1 Hz)	±30	
I_D	Drain Current	– Continuous (T_C = 25 °C)	65	A
		– Continuous (T_C = 100 °C)	41	
I_{DM}	Drain Current	– Pulsed (Note 1)	162.5	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		358	mJ
I_{AS}	Avalanche Current (Note 2)		8.1	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		4.17	mJ
dv/dt	MOSFET dv/dt		100	V/ns
	Peak Diode Recovery dv/dt (Note 3)		20	
P_D	Power Dissipation	(T_C = 25 °C)	417	W
		– Derate Above 25 °C	3.33	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		–55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8″ from Case for 5 seconds		300	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Repetitive rating: pulse width limited by maximum junction temperature.
2. I_{AS} = 8.1 A, R_G = 25 Ω, starting T_J = 25 °C.
3. $I_{SD} \le$ 32.5 A, di/dt ≤ 200 A/μs, $V_{DD} \le$ 400 V, starting T_J = 25 °C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.3	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

ELECTRICAL CHARACTERISTICS (T_C = 25 °C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA, T_J = 25 °C	650	–	–	V
		V_{GS} = 0 V, I_D = 1 mA, T_J = 150 °C	700	–	–	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 1 mA, Referenced to 25 °C	–	0.64	–	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V	–	–	1	μA
		V_{DS} = 520 V, T_C = 125 °C	–	4.5	–	
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V	–	–	±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 1.7 mA	2.5	–	4.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 32.5 A	–	35.4	40	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 32.5 A	–	46	–	S

ELECTRICAL CHARACTERISTICS (T_C = 25 °C unless otherwise noted) (continued)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 400 V, V_{GS} = 0 V, f = 1 MHz	–	4740	–	pF
C_{oss}	Output Capacitance		–	120	–	pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	–	1154	–	pF
$C_{oss(er.)}$	Energy Related Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V	–	171	–	pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	V_{DS} = 400 V, I_D = 32.5 A, V_{GS} = 10 V (Note 4)	–	136	–	nC
Q_{gs}	Gate to Source Gate Charge		–	33	–	nC
Q_{gd}	Gate to Drain “Miller” Charge		–	59	–	nC
ESR	Equivalent Series Resistance	f = 1 MHz	–	0.7	–	Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 32.5 A, V_{GS} = 10 V, R_g = 3.3 Ω (Note 4)	–	35	–	ns
t_r	Turn-On Rise Time		–	51	–	ns
$t_{d(off)}$	Turn-Off Delay Time		–	95	–	ns
t_f	Turn-Off Fall Time		–	30	–	ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
I_S	Maximum Continuous Drain to Source Diode Forward Current		–	–	65	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		–	–	162.5	A
V_{SD}	Drain to Source Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 32.5 A	–	–	1.2	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_{SD} = 32.5 A, dI_F/dt = 100 A/μs	–	534	–	ns
Q_{rr}	Reverse Recovery Charge		–	13.6	–	μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Reel Size	Tape Width	Quantity
NVHL040N65S3	NVHL040N65S3	TO-247 G03	Tube	N/A	N/A	30 Units

TYPICAL PERFORMANCE CHARACTERISTICS

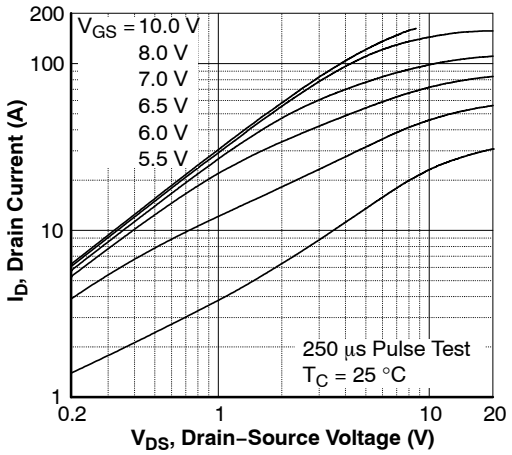


Figure 1. On−Region Characteristics 25°C

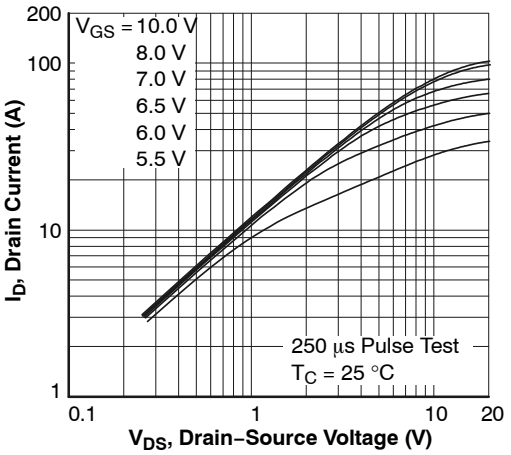


Figure 2. On−Region Characteristics 150°C

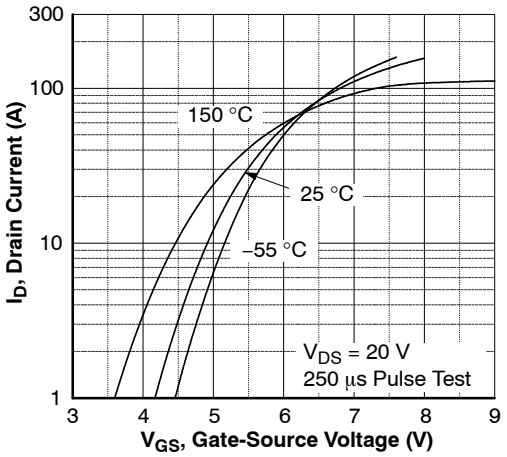


Figure 3. Transfer Characteristics

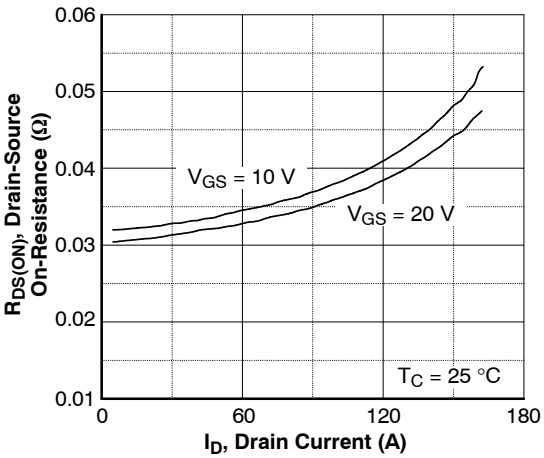


Figure 4. On-Resistance Variation vs. Drain Current and Gate Voltage

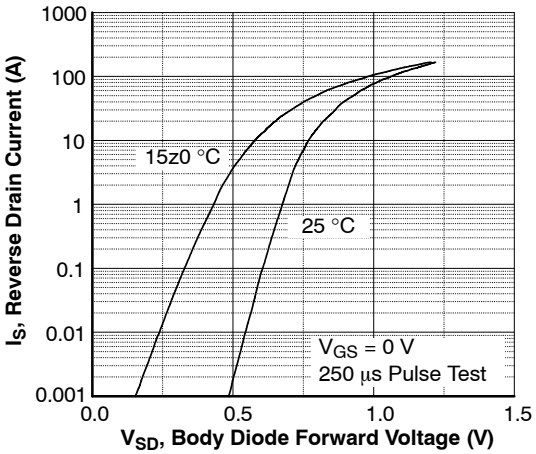


Figure 5. Body Diode Forward Voltage Variation vs. Source Current and Temperature

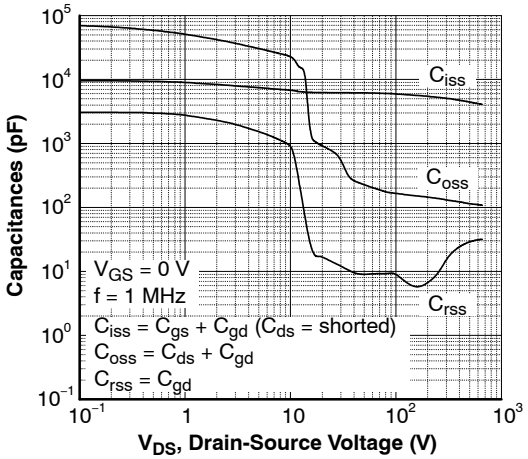


Figure 6. Capacitance Characteristics

TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)

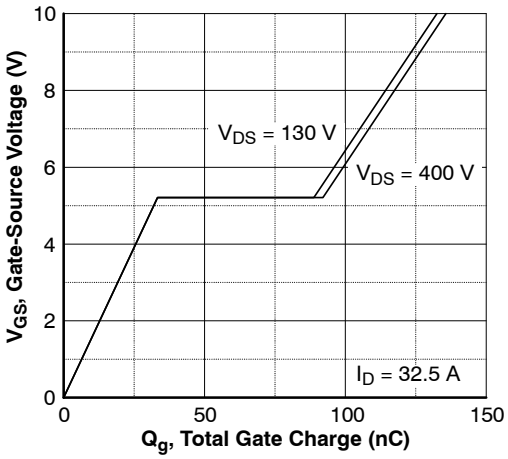


Figure 7. Gate Charge Characteristics

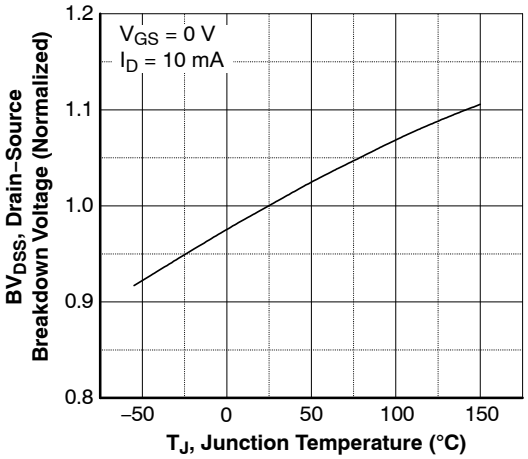


Figure 8. Breakdown Voltage Variation vs. Temperature

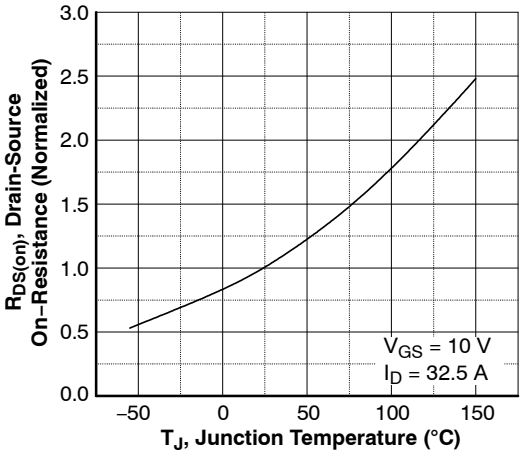


Figure 9. On-Resistance Variation vs. Temperature

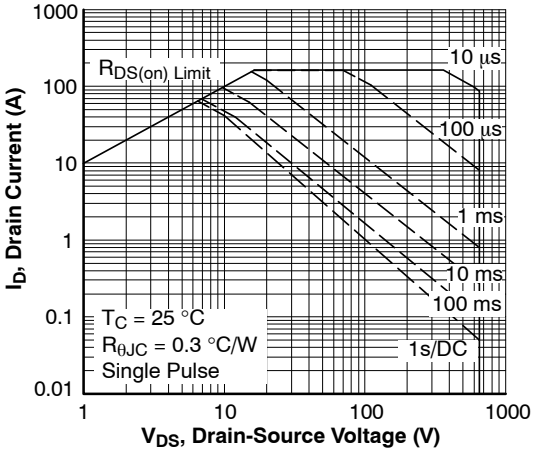


Figure 10. Maximum Safe Operating Area

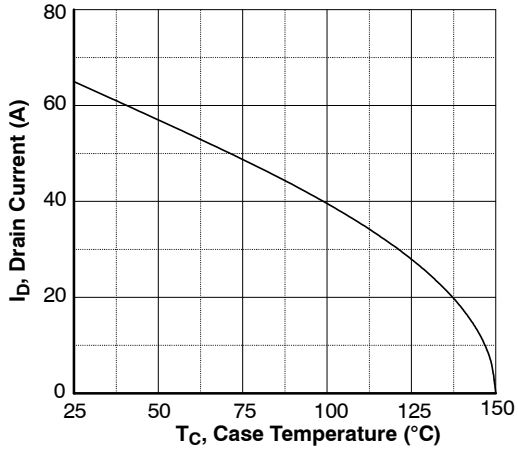


Figure 11. Maximum Drain Current vs. Case Temperature

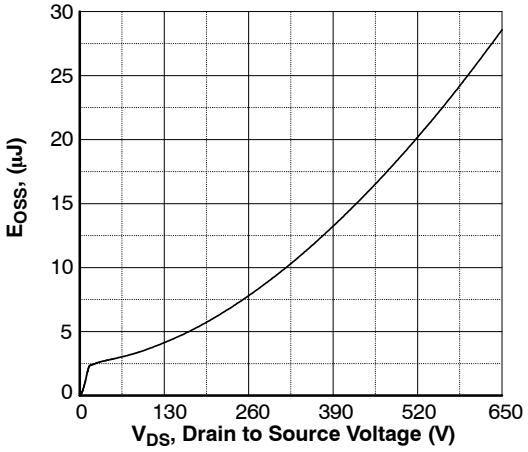


Figure 12. E_{OSS} vs. Drain to Source Voltage

TYPICAL PERFORMANCE CHARACTERISTICS (CONTINUED)

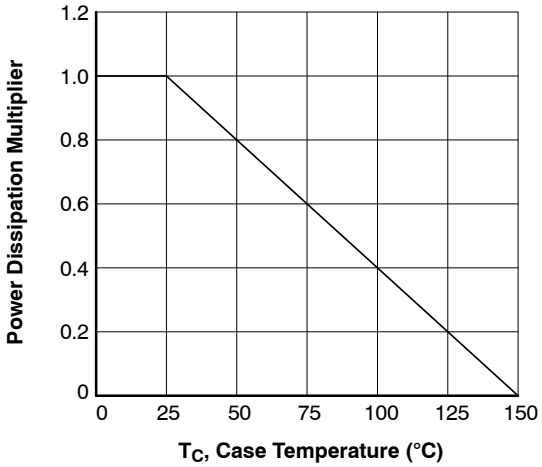


Figure 13. Normalized Power Dissipation vs. Case Temperature

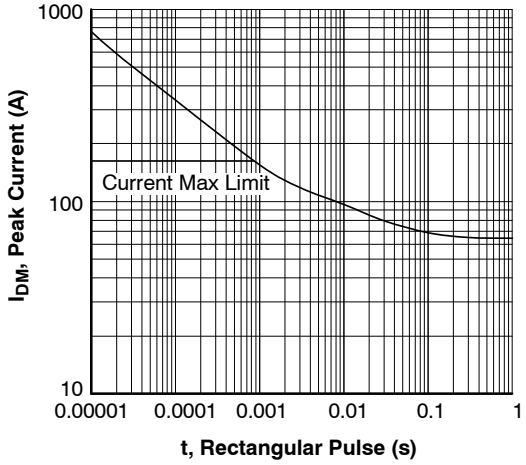


Figure 14. Peak Current Capability

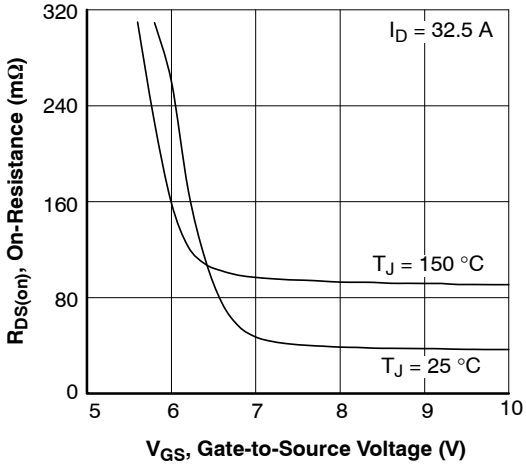


Figure 15. $R_{DS(on)}$ vs. Gate Voltage Figure

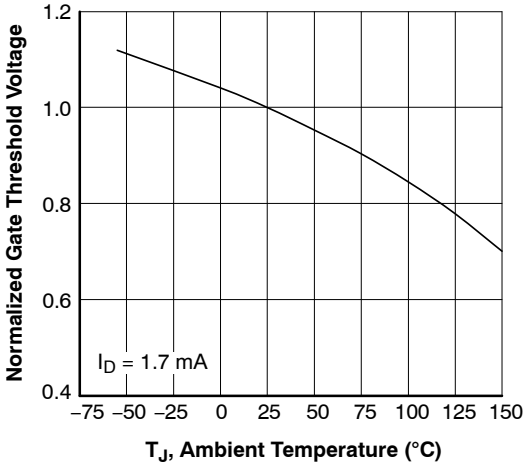


Figure 16. Normalized Gate Threshold Voltage vs. Temperature

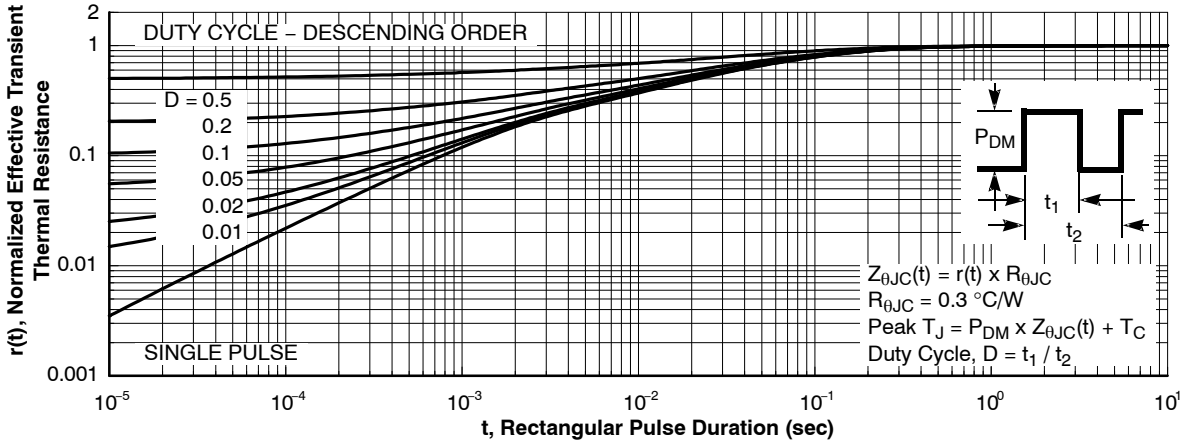


Figure 17. Transient Thermal Response Curve

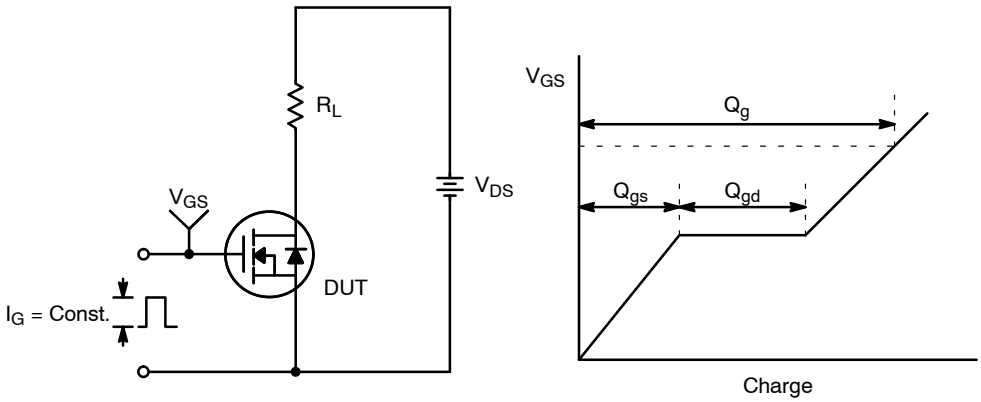


Figure 18. Gate Charge Test Circuit & Waveform

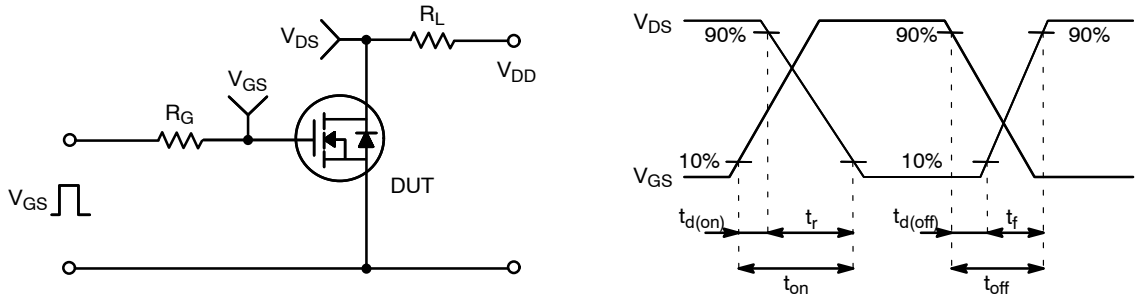


Figure 19. Resistive Switching Test Circuit & Waveforms

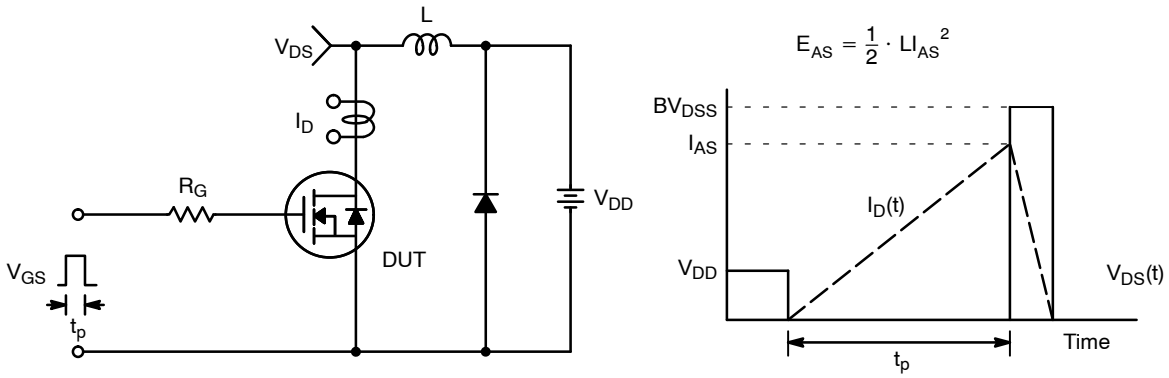


Figure 20. Unclamped Inductive Switching Test Circuit & Waveforms

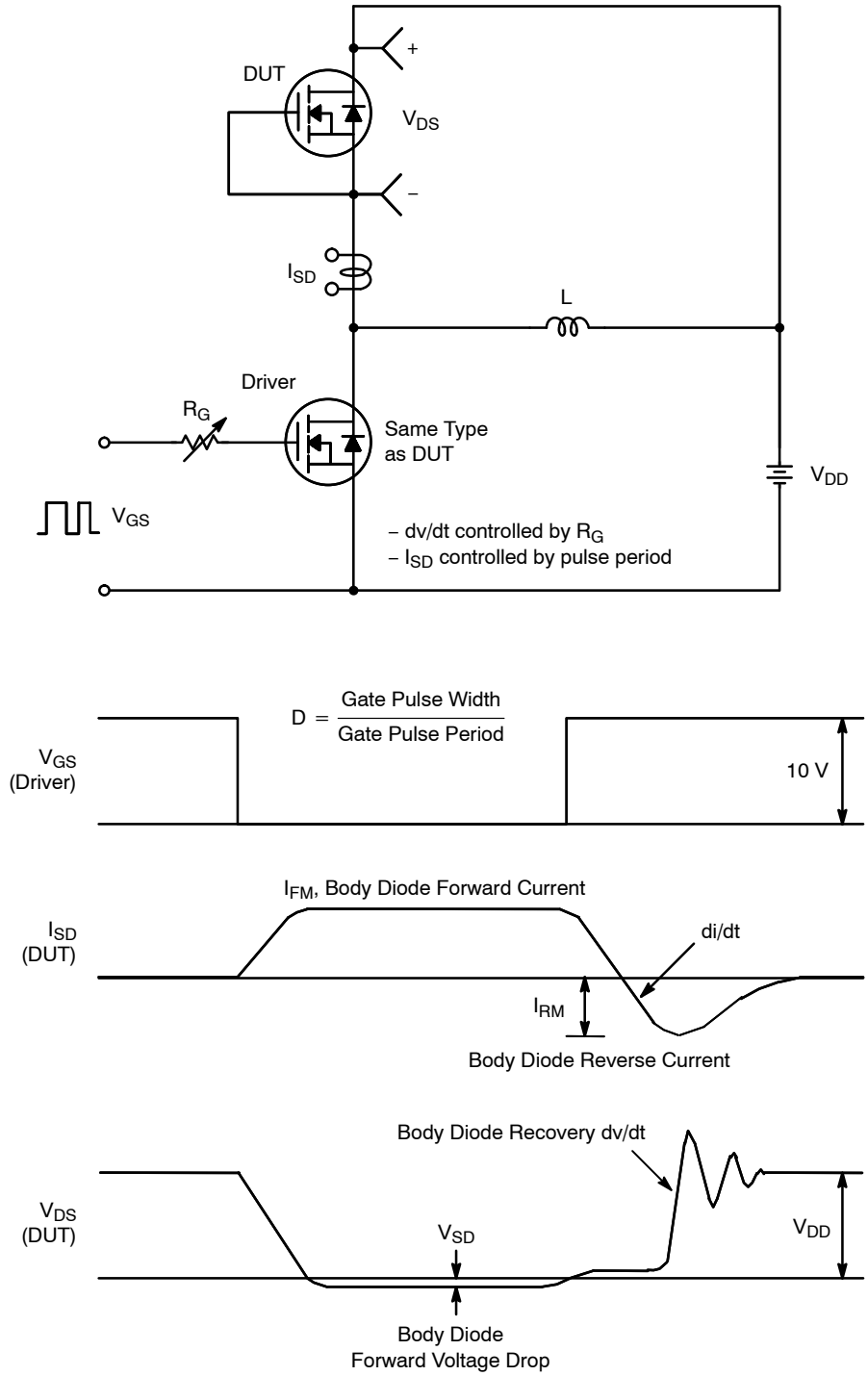


Figure 21. Peak Diode Recovery dv/dt Test Circuit & Waveforms

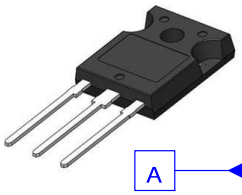
REVISION HISTORY

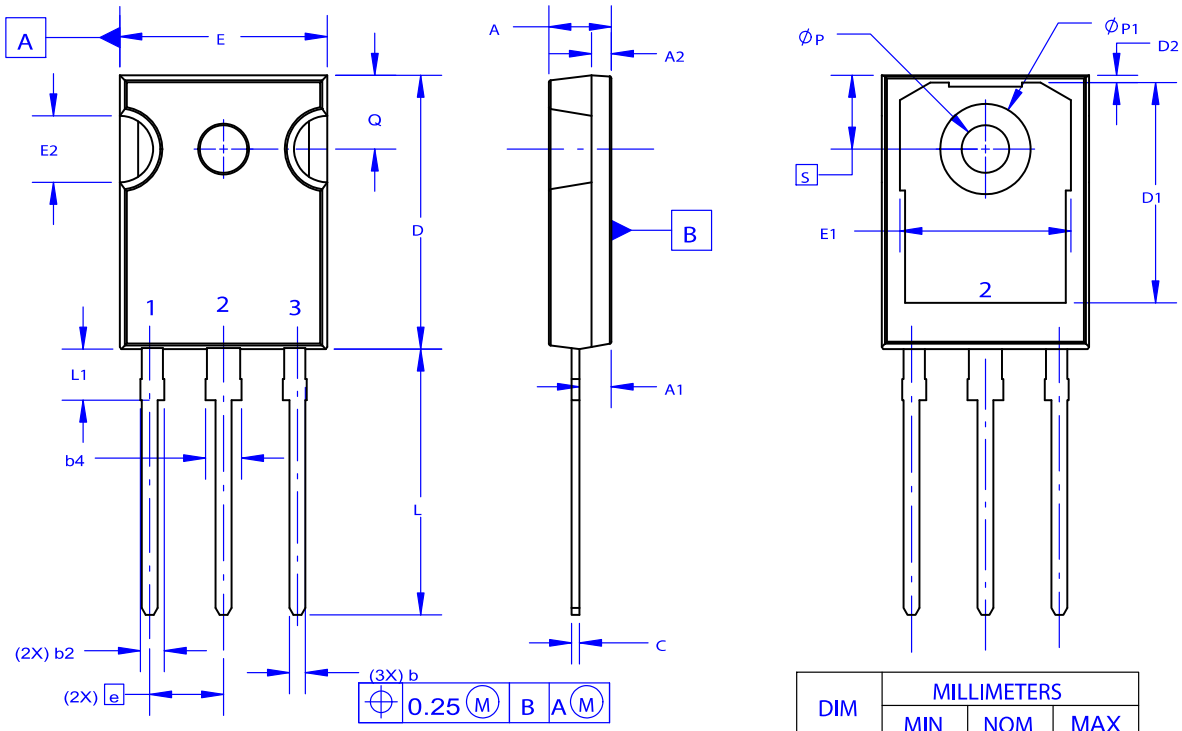
Revision	Description of Changes	Date
1	Rebranded the Data Sheet to **onsemi** format.	10/15/2025

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

TO−247−3LD
CASE 340CX
ISSUE A

DATE 06 JUL 2020





NOTES: UNLESS OTHERWISE SPECIFIED.

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
B. ALL DIMENSIONS ARE IN MILLIMETERS.
C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
ØP	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
ØP1	6.60	6.80	7.00

GENERIC MARKING DIAGRAM*

XXXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
G = Pb−Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “ ▪”, may or may not be present. Some products may not follow the Generic Marking.

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